

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	"10785293"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 08:54
L2	3273	(die near1 (attachment attached attach bonded bond bonding)) near3 (method process)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:08
L3	20	2 and (heat near (tunnel conduit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:10
L4	0	3 and (induction near heating)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:02
L5	20	2 and (heat\$3 near (tunnel conduit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:02
L6	9	2 and (induction near heating)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:05
L7	7065	(heat near (tunnel conduit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:05
L8	124	7 and (induction near1 heating)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 10:07

L9	3146	heat\$3 near1 tunnel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:05
L10	67	9 and (induction near1 heating)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:10
L11	3	10 and (chip die) and (carrier substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:07
L12	6	8 and (chip die) and (carrier substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:07
L13	18904	((die dice chip) near3 (attachment attached attach bonded bond bonding)) near4 (carrier substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 16:50
L14	76	13 and (heat\$3 near1 (tunnel conduit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:10
L15	0	14 and (induction near1 heating).	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:10
L16	0	14 and (induction near1 heat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 09:11

L17	31	13 and (induction near1 heat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 16:51
L18	3	("6288376").URPN.	USPAT	OR	ON	2005/06/16 09:14
L19	1	("6386422").URPN.	USPAT	OR	ON	2005/06/16 09:16
L20	0	("6686565").URPN.	USPAT	OR	ON	2005/06/16 09:17
L21	19	("4224927"   "4520575"   "4568277"   "4750664"   "4771929"   "4817851"   "5066850"   "5067419"   "5148583"   "5193735"   "5520320"   "5567151"   "5573688"   "5860472"   "5901462"   "6106281"   "6376817"   "6386422"   "6394796").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/16 09:17
L22	9	("5066850").URPN.	USPAT	OR	ON	2005/06/16 09:26
L23	3	("1949716"   "4938410").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/16 09:30
L24	26	("4938410").URPN.	USPAT	OR	ON	2005/06/16 09:32
L25	3	("1949716"   "4938410").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/16 09:37
L26	9	("4771929"   "5039841"   "5338008"   "5567151"   "5611476"   "5785233"   "5797539"   "6135344"   "6288376").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/16 09:38
L27	12	("2803731"   "3031554"   "3460816"   "4327265"   "4431891"   "4983804"   "4989070"   "5554836"   "5969262").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/16 09:41
L28	2059	219/388	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 10:06
L29	330	228/42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 10:06

L30	228	228/46	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 10:06
L31	2510	28 29 30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 10:07
L32	196	31 and (chip die dice) and (substrate carrier pcb (printed near1 board))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 12:47
L33	6	32 and (induct\$3 near1 heat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 12:46
L34	25	("5409543").URPN.	USPAT	OR	ON	2005/06/16 10:15
L35	1	("6423945").URPN.	USPAT	OR	ON	2005/06/16 10:34
L36	5	("4687895"   "5364007"   "5409543"   "5433368"   "5685475").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/06/16 10:34
L37	81	31 and (induct\$3 near1 heat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:34
L38	7	37 and (chip die dice) and (substrate carrier pcb board)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:35
L39	36	37 and (substrate carrier pcb board)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:27

L40	29	39 not 38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:27
L41	17	37 and (chip die dice)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:33
L42	10	41 not 38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:33
L43	55388	(induct\$3 near1 heat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 16:36
L44	858	43 and ((chip die (semiconductor near1 (component device element package)) dice) with (substrate carrier pcb board))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:36
L45	166	44 and (heat\$3 near4 (chamber tunnel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:57
L46	91	45 and coil	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:38
L47	20	46 and (solder eutectic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:50

L48	236	44 and (heat\$3 with (chamber tunnel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:50
L49	39	48 and (solder eutectic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 15:00
L50	19	49 not 47	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:51
L51	168	44 and ((heat\$3 near4 (chamber tunnel)) ((solder soldering) near1 reflow near2 (system furnace type apparatus)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 14:59
L52	29	51 and (solder eutectic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 15:00
L53	32	51 and (solder soldering soldered eutectic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 15:01
L54	24	53 not 50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 15:01
L55	231	(induct\$3 near1 heat\$3) with (infrared near1 ray)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 16:37

L56	93	(induct\$3 near1 heat\$3) near3 (infrared near1 ray)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 16:38
L57	18	(induct\$3 near1 heat\$3) near3 (far near1 infrared near1 ray)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 16:38
L58	24879	((die dice chip) near3 (attachment attached attach bonded bond bonding soldering soldered)) near4 (carrier board substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 16:50
L59	6328	58 with (method process apparatus)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 16:51
L60	15	59 and ((inductive induction inducting) near1 heat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/16 16:52